

2SK2277

Silicon N-Channel MOS

For switching

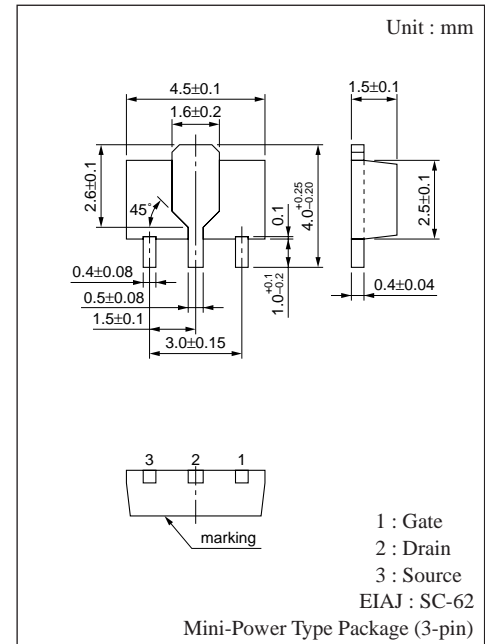
■ Features

- Low ON-resistance $R_{DS(on)}$
- High-speed switching
- Downsizing of sets by mini-type package and automatic insertion by magazine packing are available.

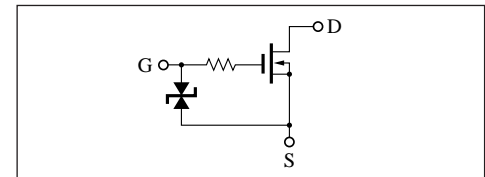
■ Absolute Maximum Ratings (Ta = 25°C)

Parameter	Symbol	Rating	Unit
Drain-Source breakdown voltage	V_{DS}	60	V
Gate-Source voltage	V_{GSO}	± 20	V
Drain current	I_D	± 1	A
Max drain current	I_{PD}	± 2	A
Allowable power dissipation	P_D^*	1	W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

* PC board : Copper foil area of drain portion should be 1cm² or more, thickness 1.7mm.



■ Internal Connection



■ Electrical Characteristics (Ta = 25°C)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source cut-off current	I_{DSS}	$V_{DS}=50V, V_{GS}=0$			10	μA
Gate-Source leakage current	I_{GSS}	$V_{GS}=\pm 15V, V_{DS}=0$			± 10	μA
Drain-Source breakdown voltage	V_{DSS}	$I_D=0.1mA, V_{GS}=0$	60			V
Gate-Source voltage	V_{GSS}	$I_{GS}=0.1mA, V_{DS}=0$	± 20			V
Gate threshold voltage	V_{th}	$V_{DS}=5V, I_D=1mA$	0.8		2	V
Drain-Source ON-resistance	$R_{DS(on)}^{1*1}$	$V_{GS}=4V, I_D=0.5A$		0.72	1	Ω
	$R_{DS(on)}^{2*1}$	$V_{GS}=10V, I_D=0.5A$		0.55	0.85	Ω
Forward transadmittance	$ Y_{fs} ^{*1}$	$V_{DS}=10V, I_D=0.5A$	0.5			S
Input capacitance	C_{iss}	$V_{DS}=10V, V_{GS}=0, f=1MHz$		75		pF
Output capacitance	C_{oss}			30		pF
Feedback capacitance	C_{rss}			7		pF
Turn-on time	t_{on}	$V_{GS}=10V, I_D=0.5A$ $V_{DD}=10V, R_L=20\Omega$		35		ns
Fall time	t_f			80		ns
Turn-off time (delay time)	$t_{d(off)}$			130		ns

* 1 Pulse measurement

■ Marking

